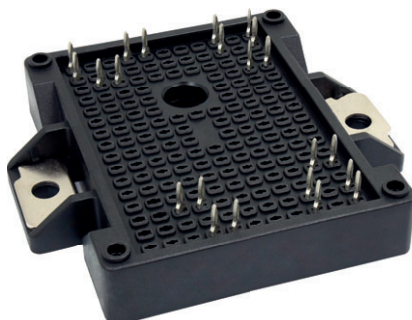


EMIPAK-2B PressFit Power Module

3-Levels Half-Bridge Inverter Stage, 75 A



EMIPAK-2B
(package example)

FEATURES

- Trench IGBT technology
- FRED Pt® clamping diodes
- PressFit pins technology
- Exposed Al₂O₃ substrate with low thermal resistance
- Short circuit rated
- Square RBSOA
- Integrated thermistor
- Low internal inductances
- Low switching loss
- PressFit pins locking technology. Patent # US.263.820 B2
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

PRODUCT SUMMARY

Q1 - Q4 IGBT STAGE	
V _{CES}	600 V
V _{CE(ON)} typical at I _C = 75 A	1.7 V
I _C at T _C = 89 °C	75 A
Q2 - Q3 IGBT STAGE	
V _{CES}	600 V
V _{CE(ON)} typical at I _C = 75 A	1.56 V
I _C at T _C = 122 °C	75 A
Speed	8 kHz to 30 kHz
Package	EMIPAK-2B
Circuit	3-levels half bridge inverter stage

DESCRIPTION

VS-ETF075Y60U is an integrated solution for a multi level inverter stage in a single package. The EMIPAK-2B package is easy to use thanks to the PressFit pins and the exposed substrate provides improved thermal performance. The optimized layout also helps to minimize stray parameters, allowing for better EMI performance.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Operating junction temperature	T _J		175	°C
Storage temperature range	T _{Stg}		-40 to +150	
RMS isolation voltage	V _{ISOL}	T _J = 25 °C, all terminals shorted, f = 50 Hz, t = 1 s	3500	V
Q1 - Q4 IGBT				
Collector to emitter voltage	V _{CES}		600	V
Gate to emitter voltage	V _{GES}		20	
Pulsed collector current	I _{CM}		200	A
Clamped inductive load current	I _{LM} ⁽¹⁾		200	
Continuous collector current	I _C	T _C = 25 °C	109	A
		T _C = 80 °C	80	
		T _{SINK} = 80 °C	40	
Power dissipation	P _D	T _C = 25 °C	294	W
		T _C = 80 °C	186	

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and International patents.



ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Q2 - Q3 IGBT				
Collector to emitter voltage	V _{CES}		600	V
Gate to emitter voltage	V _{GES}		20	
Pulsed collector current	I _{CM}		250	A
Clamped inductive load current	I _{LM} ⁽¹⁾		250	
Continuous collector current	I _C	T _C = 25 °C	154	A
		T _C = 80 °C	113	
		T _{SINK} = 80 °C	50	
Power dissipation	P _D	T _C = 25 °C	405	W
		T _C = 80 °C	257	
D5 - D6 CLAMPING DIODE				
Repetitive peak reverse voltage	V _{RRM}		600	V
Single pulse forward current	I _{FSM}	10 ms sine or 6 ms rectangular pulse, T _J = 25 °C	270	A
Diode continuous forward current	I _F	T _C = 25 °C	78	
		T _C = 80 °C	55	
		T _{SINK} = 80 °C	28	
Power dissipation	P _D	T _C = 25 °C	174	W
		T _C = 80 °C	110	
D1 - D2 - D3 - D4 AP DIODE				
Single pulse forward current	I _{FSM}	10 ms sine or 6 ms rectangular pulse, T _J = 25 °C	250	A
Diode continuous forward current	I _F	T _C = 25 °C	72	
		T _C = 80 °C	70	
		T _{SINK} = 80 °C	31	
Power dissipation	P _D	T _C = 25 °C	107	W
		T _C = 80 °C	68	

Notes

- Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur.
- (1) $V_{CC} = 300\text{ V}$, $V_{GE} = 15\text{ V}$, $L = 500\text{ }\mu\text{H}$, $R_g = 4.7\text{ }\Omega$, $T_J = 175\text{ }^{\circ}\text{C}$



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q1 - Q4 IGBT						
Collector to emitter breakdown voltage	BV _{CES}	V _{GE} = 0 V, I _C = 100 μA	600	-	-	V
Collector to emitter voltage	V _{CE(ON)}	V _{GE} = 15 V, I _C = 60 A	-	1.57	1.8	V
		V _{GE} = 15 V, I _C = 75 A	-	1.7	1.93	
		V _{GE} = 15 V, I _C = 60 A, T _J = 125 °C	-	1.7	-	
		V _{GE} = 15 V, I _C = 75 A, T _J = 125 °C	-	1.86	-	
Gate threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 2.1 mA	3.6	5.6	7.1	
Temperature coefficient of threshold voltage	ΔV _{GE(th)} /ΔT _J	V _{CE} = V _{GE} , I _C = 1 mA (25 °C to 125 °C)	-	-12	-	mV/°C
Forward transconductance	g _{fe}	V _{CE} = 20 V, I _C = 75 A	-	51	-	S
Transfer characteristics	V _{GE}	V _{CE} = 20 V, I _C = 75 A	-	9.6	-	V
Zero gate voltage collector current	I _{CES}	V _{GE} = 0 V, V _{CE} = 600 V	-	0.0002	0.1	mA
		V _{GE} = 0 V, V _{CE} = 600 V, T _J = 125 °C	-	0.01	-	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V, V _{CE} = 0 V	-	-	± 200	nA
Q2 - Q3 IGBT						
Collector to emitter breakdown voltage	BV _{CES}	V _{GE} = 0 V, I _C = 500 μA	600	-	-	V
Collector to emitter voltage	V _{CE(ON)}	V _{GE} = 15 V, I _C = 60 A	-	1.45	1.62	V
		V _{GE} = 15 V, I _C = 75 A	-	1.56	1.73	
		V _{GE} = 15 V, I _C = 60 A, T _J = 125 °C	-	1.52	-	
		V _{GE} = 15 V, I _C = 75 A, T _J = 125 °C	-	1.67	-	
Gate threshold voltage	V _{GE(th)}	V _{CE} = V _{GE} , I _C = 5.6 mA	3.6	5.3	7.1	
Temperature coefficient of threshold voltage	ΔV _{GE(th)} /ΔT _J	V _{CE} = V _{GE} , I _C = 1.4 mA (25 °C to 125 °C)	-	-18	-	mV/°C
Forward transconductance	g _{fe}	V _{CE} = 20 V, I _C = 75 A	-	72	-	S
Transfer characteristics	V _{GE}	V _{CE} = 20 V, I _C = 75 A	-	8.3	-	V
Zero gate voltage collector current	I _{CES}	V _{GE} = 0 V, V _{CE} = 600 V	-	0.0005	0.1	mA
		V _{GE} = 0 V, V _{CE} = 600 V, T _J = 125 °C	-	0.065	-	
Gate to emitter leakage current	I _{GES}	V _{GE} = ± 20 V, V _{CE} = 0 V	-	-	± 400	nA
D5 - D6 CLAMPING DIODE						
Cathode to anode blocking voltage	V _{BR}	I _R = 100 μA	600	-	-	V
Forward voltage drop	V _{FM}	I _F = 40 A	-	1.83	2.35	
		I _F = 40 A, T _J = 125 °C	-	1.51	-	
Reverse leakage current	I _{RM}	V _R = 600 V	-	0.0002	0.1	mA
		V _R = 600 V, T _J = 125 °C	-	0.028	-	
D1 - D2 - D3 - D4 AP DIODE						
Forward voltage drop	V _{FM}	I _F = 30 A	-	1.2	1.41	V
		I _F = 30 A, T _J = 125 °C	-	1.06	-	



SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Q1 - Q4 IGBT (WITH D5 - D6 CLAMPING DIODE)						
Total gate charge (turn-on)	Q_g	$I_C = 75\text{ A}$ $V_{CC} = 400\text{ V}$ $V_{GE} = 15\text{ V}$	-	150	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	40	-	
Gate to collector charge (turn-on)	Q_{gc}		-	60	-	
Turn-on switching loss	E_{ON}	$I_C = 75\text{ A}$ $V_{CC} = 300\text{ V}$ $V_{GE} = 15\text{ V}$	-	0.94	-	mJ
Turn-off switching loss	E_{OFF}		-	1.1	-	
Total switching loss	E_{TOT}		-	2.04	-	
Turn-on delay time	$t_{d(on)}$	$R_g = 4.7\text{ }\Omega$ $L = 500\text{ }\mu\text{H}^{(1)}$	-	78	-	ns
Rise time	t_r		-	72	-	
Turn-off delay time	$t_{d(off)}$		-	101	-	
Fall time	t_f		-	65	-	
Turn-on switching loss	E_{ON}	$I_C = 75\text{ A}$ $V_{CC} = 300\text{ V}$ $V_{GE} = 15\text{ V}$	-	1.13	-	mJ
Turn-off switching loss	E_{OFF}		-	1.61	-	
Total switching loss	E_{TOT}		-	2.74	-	
Turn-on delay time	$t_{d(on)}$	$R_g = 4.7\text{ }\Omega$ $L = 500\text{ }\mu\text{H}$ $T_J = 125\text{ }^{\circ}\text{C}^{(1)}$	-	78	-	ns
Rise time	t_r		-	72	-	
Turn-off delay time	$t_{d(off)}$		-	106	-	
Fall time	t_f		-	107	-	
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1\text{ MHz}$	-	4440	-	pF
Output capacitance	C_{oes}		-	245	-	
Reverse transfer capacitance	C_{res}		-	130	-	
Reverse bias safe operating area	RBSOA	$T_J = 175\text{ }^{\circ}\text{C}$, $I_C = 200\text{ A}$, $V_{CC} = 300\text{ V}$, $V_P = 600\text{ V}$, $R_g = 4.7\text{ }\Omega$, $V_{GE} = 15\text{ V}$ to 0 V	Fullsquare			
Short circuit safe operating area	SCSOA	$R_g = 10\text{ }\Omega$, $V_{CC} = 400\text{ V}$, $V_P = 600\text{ V}$ $V_{GE} = 15\text{ V}$ to 0	-	-	5	μs
Q2 - Q3 IGBT (WITH FREEWHEELING EXTERNAL TO-247 DIODE DISCRETE 30ETH06)						
Total gate charge (turn-on)	Q_g	$I_C = 120\text{ A}$ $V_{CC} = 400\text{ V}$ $V_{GE} = 15\text{ V}$	-	240	-	nC
Gate to emitter charge (turn-on)	Q_{ge}		-	69	-	
Gate to collector charge (turn-on)	Q_{gc}		-	90	-	
Turn-on switching loss	E_{ON}	$I_C = 75\text{ A}$ $V_{CC} = 300\text{ V}$ $V_{GE} = 15\text{ V}$	-	0.85	-	mJ
Turn-off switching loss	E_{OFF}		-	1.54	-	
Total switching loss	E_{TOT}		-	2.39	-	
Turn-on delay time	$t_{d(on)}$	$R_g = 4.7\text{ }\Omega$ $L = 500\text{ }\mu\text{H}^{(1)}$	-	111	-	ns
Rise time	t_r		-	81	-	
Turn-off delay time	$t_{d(off)}$		-	130	-	
Fall time	t_f		-	74	-	
Turn-on switching loss	E_{ON}	$I_C = 75\text{ A}$ $V_{CC} = 300\text{ V}$ $V_{GE} = 15\text{ V}$	-	1.0	-	mJ
Turn-off switching loss	E_{OFF}		-	1.83	-	
Total switching loss	E_{TOT}		-	2.83	-	
Turn-on delay time	$t_{d(on)}$	$R_g = 4.7\text{ }\Omega$ $L = 500\text{ }\mu\text{H}$ $T_J = 125\text{ }^{\circ}\text{C}^{(1)}$	-	111	-	ns
Rise time	t_r		-	83	-	
Turn-off delay time	$t_{d(off)}$		-	140	-	
Fall time	t_f		-	104	-	
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1\text{ MHz}$	-	7750	-	pF
Output capacitance	C_{oes}		-	550	-	
Reverse transfer capacitance	C_{res}		-	225	-	
Reverse bias safe operating area	RBSOA	$T_J = 175\text{ }^{\circ}\text{C}$, $I_C = 250\text{ A}$, $V_{CC} = 300\text{ V}$, $V_P = 600\text{ V}$, $R_g = 4.7\text{ }\Omega$, $V_{GE} = 15\text{ V}$ to 0 V	Fullsquare			
Short circuit safe operating area	SCSOA	$R_g = 10\text{ }\Omega$, $V_{CC} = 400\text{ V}$, $V_P = 600\text{ V}$ $V_{GE} = 15\text{ V}$ to 0	-	-	5	μs

**SWITCHING CHARACTERISTICS** ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
D5 - D6 CLAMPING DIODE						
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs	-	59	-	ns
Diode peak reverse current	I _{rr}		-	8.5	-	A
Diode recovery charge	Q _{rr}		-	257	-	nC
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs, T _J = 125 °C	-	110	-	ns
Diode peak reverse current	I _{rr}		-	18.5	-	A
Diode recovery charge	Q _{rr}		-	1020	-	nC
D1 - D2 - D3 - D4 AP DIODE						
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs	-	108	-	ns
Diode peak reverse current	I _{rr}		-	19.5	-	A
Diode recovery charge	Q _{rr}		-	1062	-	nC
Diode reverse recovery time	t _{rr}	V _R = 200 V I _F = 50 A dI/dt = 500 A/μs, T _J = 125 °C	-	174	-	ns
Diode peak reverse current	I _{rr}		-	31	-	A
Diode recovery charge	Q _{rr}		-	2716	-	nC

Note

(1) Energy losses include “tail” and diode reverse recovery.

INTERNAL NTC - THERMISTOR SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNITS
Resistance	R_{25}	$T_C = 25\text{ }^{\circ}\text{C}$	5000	Ω
	R_{100}	$T_C = 100\text{ }^{\circ}\text{C}$	$493 \pm 5\%$	
B-value	$B_{25/50}$	$R_2 = R_{25} \exp. [B_{25/50} (1/T_2 - 1/(298.15\text{ K}))]$	$3375 \pm 5\%$	K
Maximum operating temperature			220	$^{\circ}\text{C}$
Dissipation constant			2	mW/ $^{\circ}\text{C}$
Thermal time constant			8	s

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Q1 - Q4 IGBT - Junction to case thermal resistance (per switch)	R_{thJC}	-	-	0.51	$^{\circ}\text{C}/\text{W}$
Q2 - Q3 IGBT - Junction to case thermal resistance (per switch)		-	-	0.37	
D5 - D6 Clamping diode - Junction to case thermal resistance (per diode)		-	-	0.86	
D1 - D2 - D3 - D4 AP diode - Junction to case thermal resistance (per diode)		-	-	1.4	
Q1 - Q4 IGBT - Case to sink thermal resistance (per switch)	$R_{thCS}^{(1)}$	-	0.84	-	
Q2 - Q3 IGBT - Case to sink thermal resistance (per switch)		-	0.8	-	
D5 - D6 Clamping diode - Case to sink thermal resistance (per diode)		-	1.16	-	
D1 - D2 - D3 - D4 AP diode - Case to sink thermal resistance (per diode)		-	1.12	-	
Case to sink thermal resistance per module		-	0.1	-	$^{\circ}\text{C}/\text{W}$
Mounting torque (M4)		2	-	3	Nm
Weight		-	45	-	g

Note

(1) Mounting surface flat, smooth, and greased

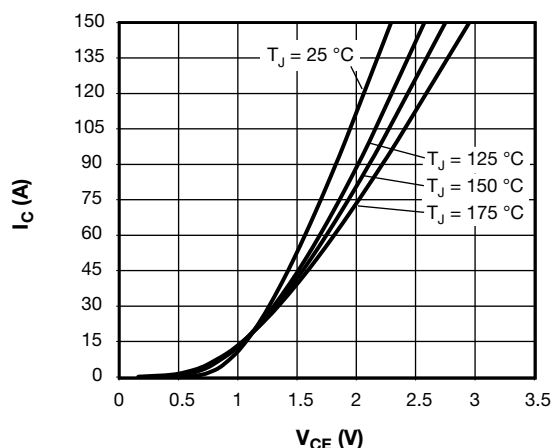


Fig. 1 - Typical Q1 - Q4 Trench IGBT Output Characteristics
 $V_{GE} = 15\text{ V}$

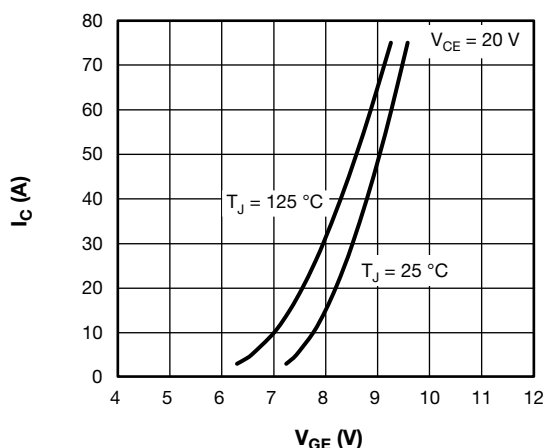


Fig. 4 - Typical Q1 - Q4 Trench IGBT Transfer Characteristics
 $V_{CE} = 20\text{ V}$

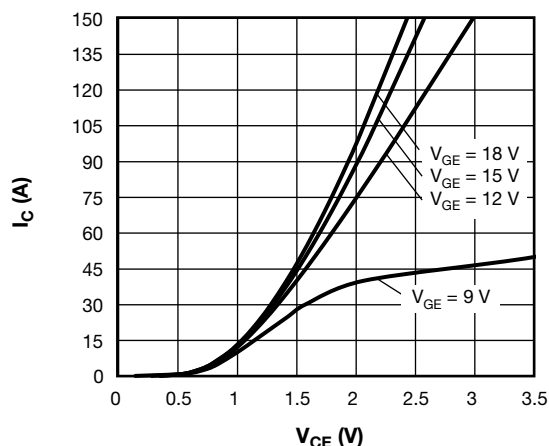


Fig. 2 - Typical Q1 - Q4 Trench IGBT Output Characteristics
 $T_J = 125\text{ °C}$

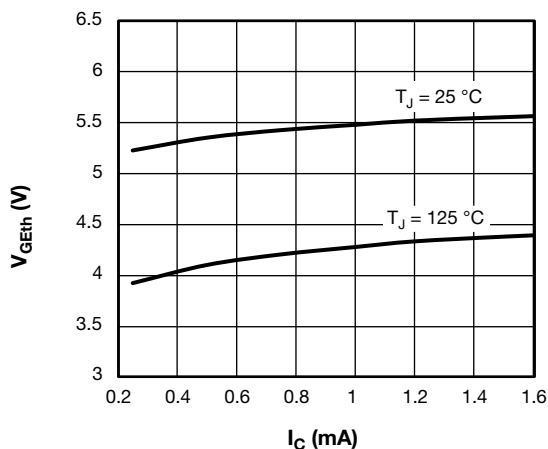


Fig. 5 - Typical Q1 - Q4 Trench IGBT Gate Threshold Voltage

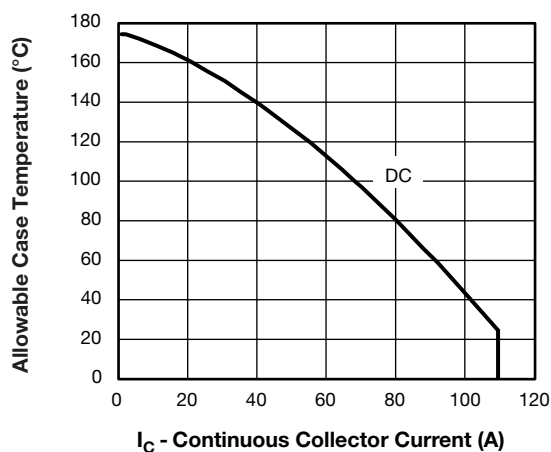


Fig. 3 - Maximum Q1 - Q4 Trench IGBT Continuous Collector Current vs. Case Temperature

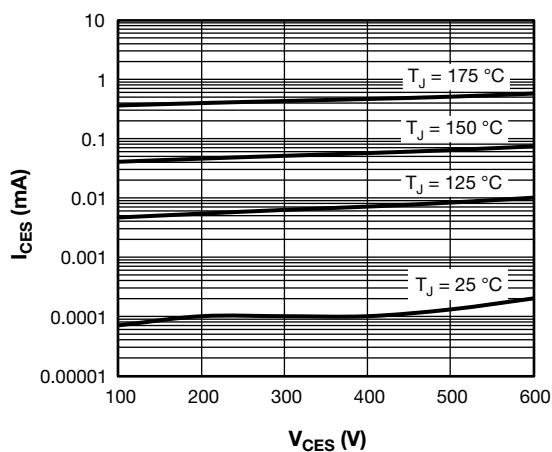


Fig. 6 - Typical Q1 - Q4 Trench IGBT Zero Gate Voltage Collector Current

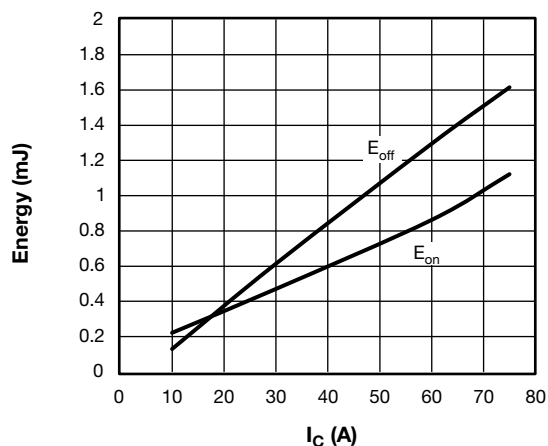


Fig. 7 - Typical Q1 - Q4 Trench IGBT Energy Loss vs. I_C
(with D5 - D6 Clamping Diode)
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

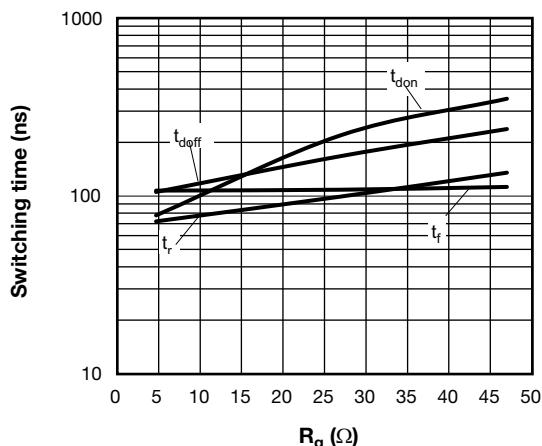


Fig. 10 - Typical Q1 - Q4 Trench IGBT Switching Time vs. R_g
(with D5 - D6 Clamping Diode)
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 75\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

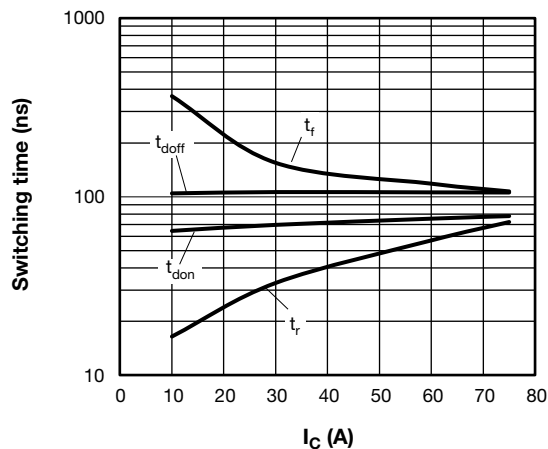


Fig. 8 - Typical Q1 - Q4 Trench IGBT Switching Loss vs. I_C
(with D5 - D6 Clamping Diode)
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

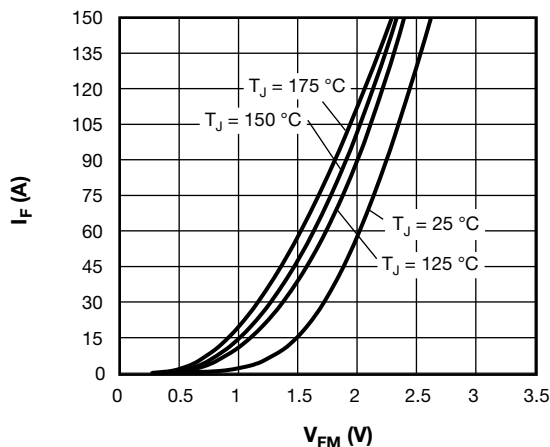


Fig. 11 - Typical D5 - D6 Clamping Diode Forward Characteristics

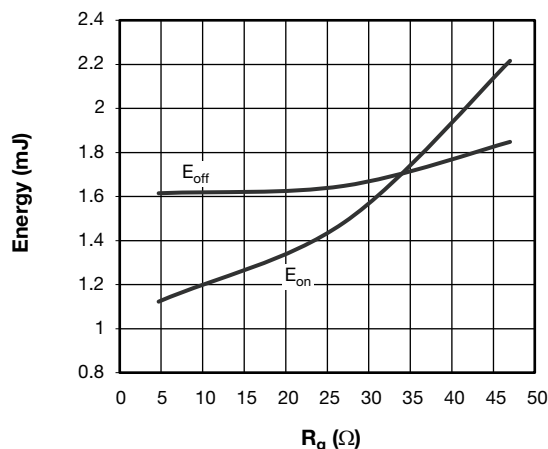


Fig. 9 - Typical Q1 - Q4 Trench IGBT Energy Loss vs. R_g
(with D5 - D6 Clamping Diode)
 $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 75\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

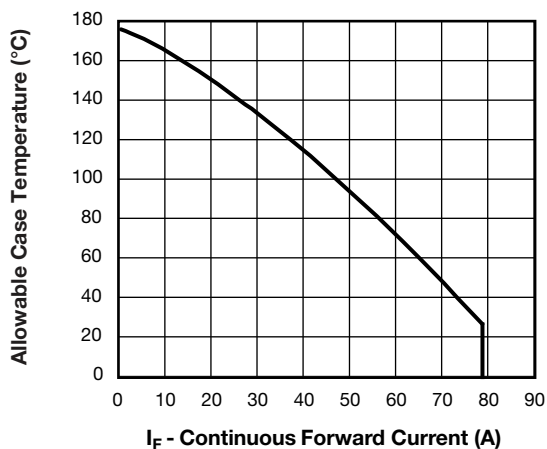


Fig. 12 - Maximum D5 - D6 Clamping Diode Forward Current vs. Case Temperature

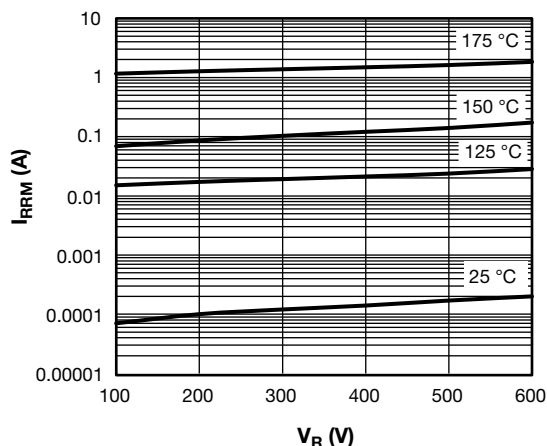
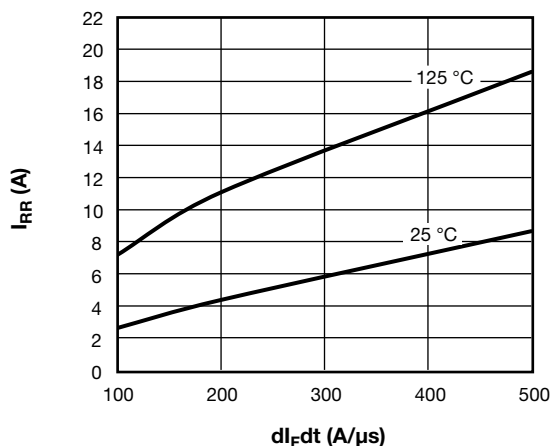
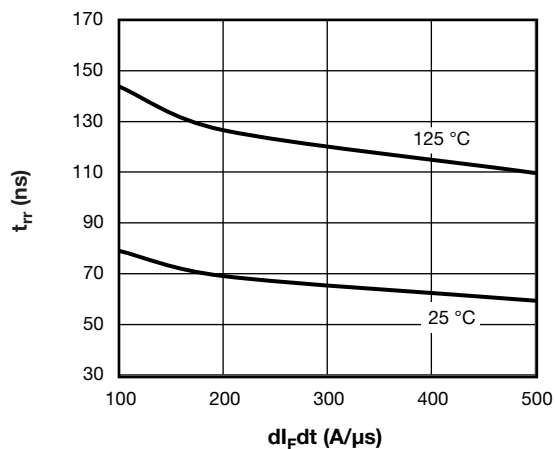
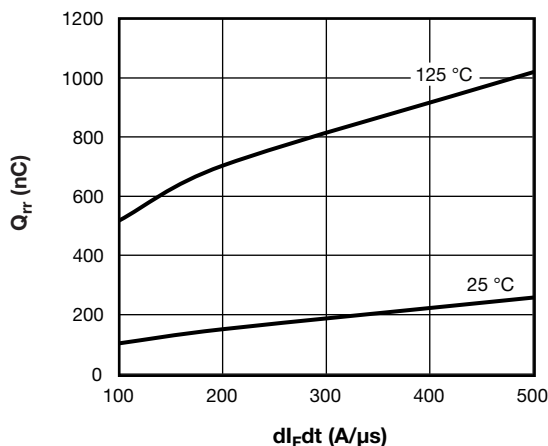
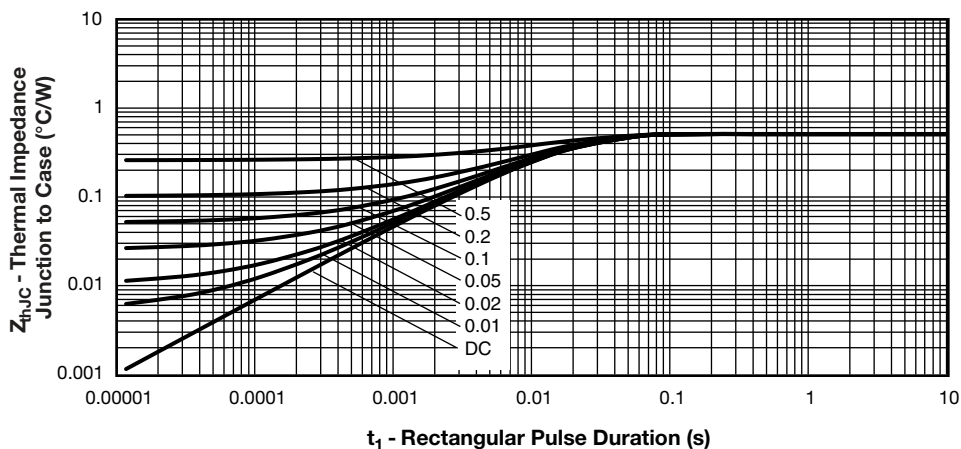


Fig. 13 - Typical D5 - D6 Clamping Diode Reverse Leakage Current


Fig. 15 - Typical D5 - D6 Clamping Diode Reverse Recovery Current vs. dI_F/dt , $V_R = 200$ V, $I_F = 50$ A

Fig. 14 - Typical D5 - D6 Clamping Diode Reverse Recovery Time vs. dI_F/dt , $V_R = 200$ V, $I_F = 50$ A

Fig. 16 - Typical D5 - D6 Clamping Diode Reverse Recovery Charge vs. dI_F/dt , $V_R = 200$ V, $I_F = 50$ A

Fig. 17 - Maximum Thermal Impedance Z_{thJC} Characteristics (Q1 - Q4 Trench IGBT)

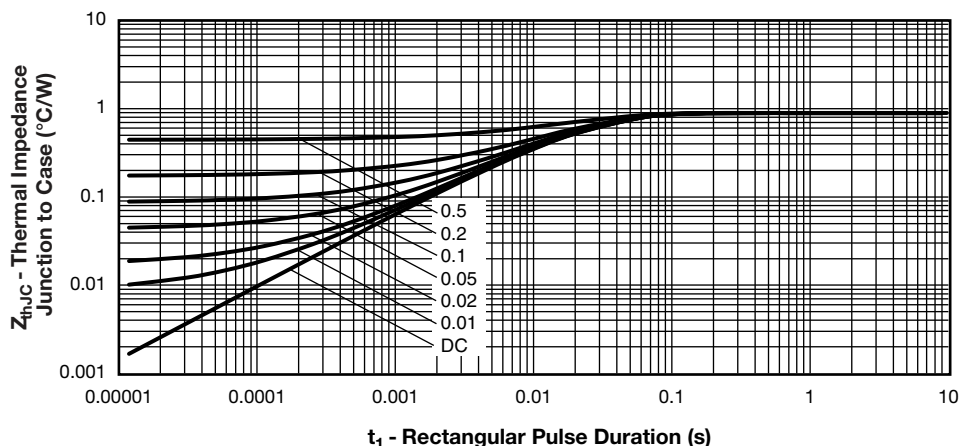


Fig. 18 - Maximum Thermal Impedance Z_{thJC} Characteristics (D5 - D6 Clamping Diode)

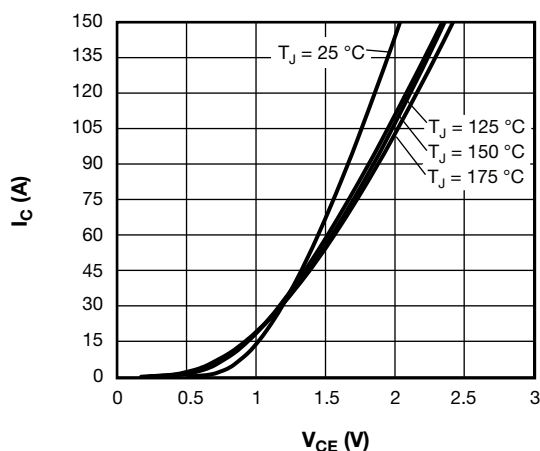


Fig. 19 - Typical Q2 - Q3 Trench IGBT Output Characteristics
 $V_{GE} = 15\text{ V}$

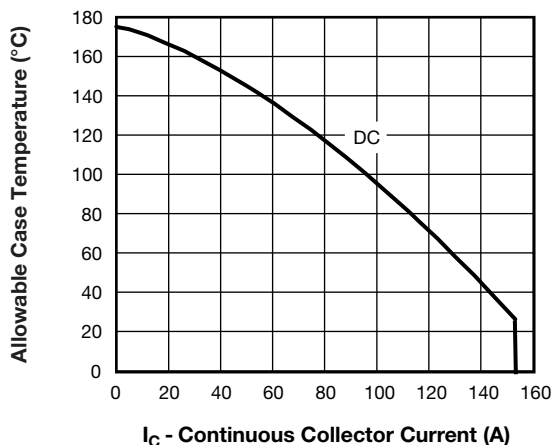


Fig. 21 - Maximum Q2 - Q3 Trench IGBT Continuous Collector Current vs. Case Temperature

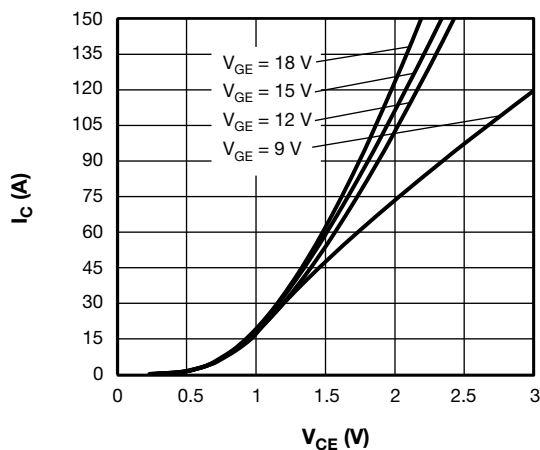


Fig. 20 - Typical Q2 - Q3 Trench IGBT Output Characteristics
 $T_J = 125\text{ °C}$

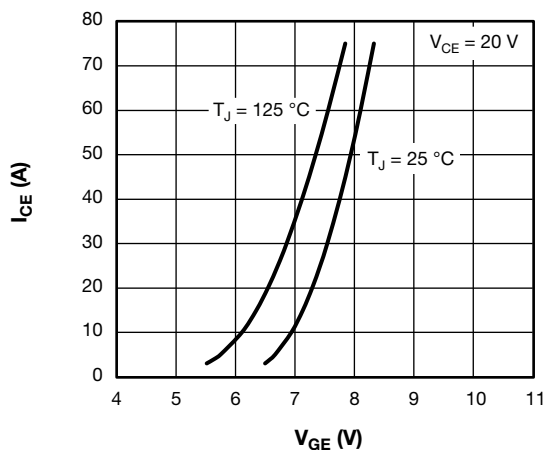


Fig. 22 - Typical Q2 - Q3 Trench IGBT Transfer Characteristics

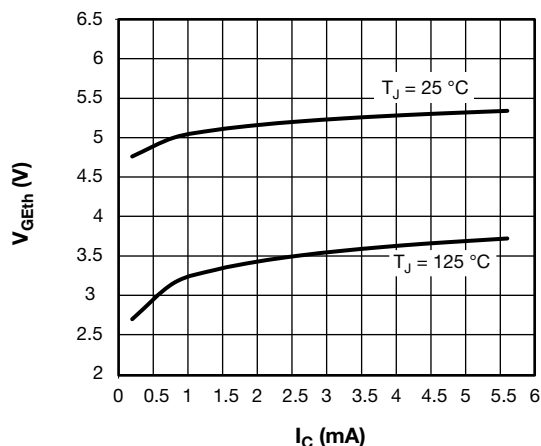


Fig. 23 - Typical Q2 - Q3 Trench IGBT Gate Threshold Voltage

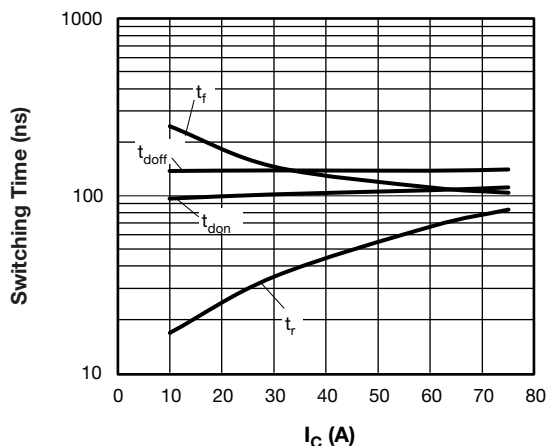
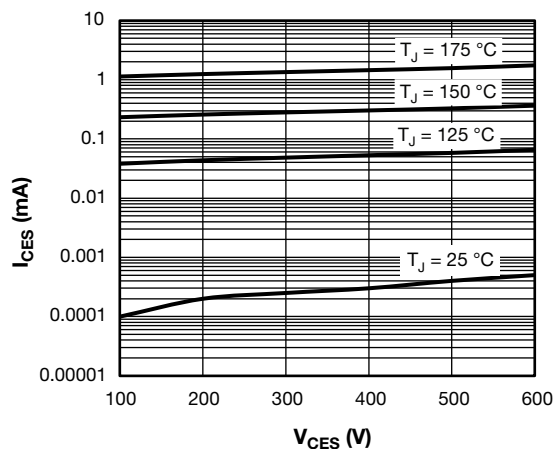
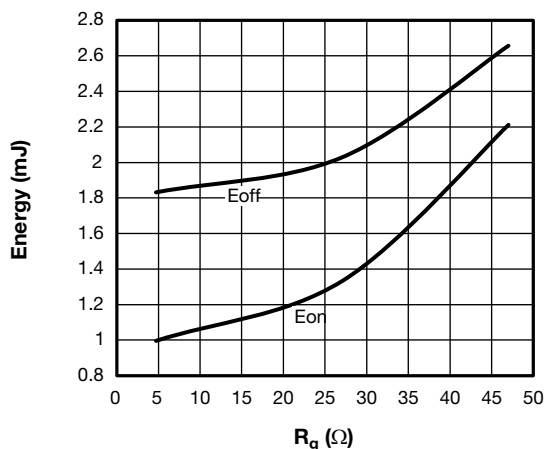
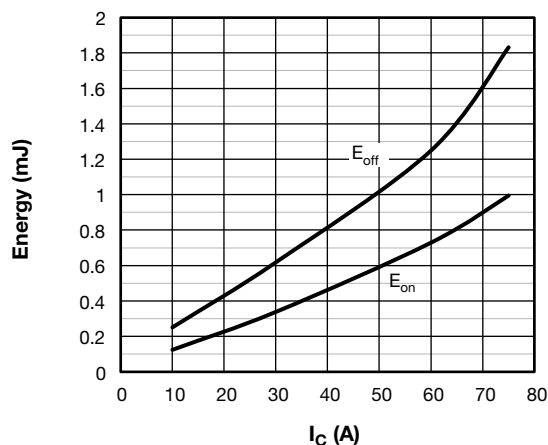
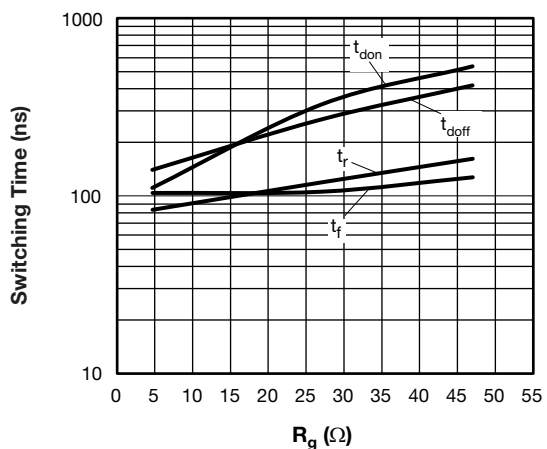

Fig. 26 - Typical Q2 - Q3 Trench IGBT Switching Time vs. I_C (with Freewheeling External TO-247 Diode Discrete 30ETH06), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$


Fig. 24 - Typical Q2 - Q3 Trench IGBT Zero Gate Voltage Collector Current


Fig. 27 - Typical Q2 - Q3 Trench IGBT Energy Loss vs. R_g (with Freewheeling External TO-247 Diode Discrete 30ETH06), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 75\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

Fig. 25 - Typical Q2 - Q3 Trench IGBT Energy Loss vs. I_C (with Freewheeling External TO-247 Diode Discrete 30ETH06), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $R_g = 4.7\ \Omega$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

Fig. 28 - Typical Q2 - Q3 Trench IGBT Switching Time vs. R_g (with Freewheeling External TO-247 Diode Discrete 30ETH06), $T_J = 125^\circ\text{C}$, $V_{CC} = 300\text{ V}$, $I_C = 75\text{ A}$, $V_{GE} = 15\text{ V}$, $L = 500\ \mu\text{H}$

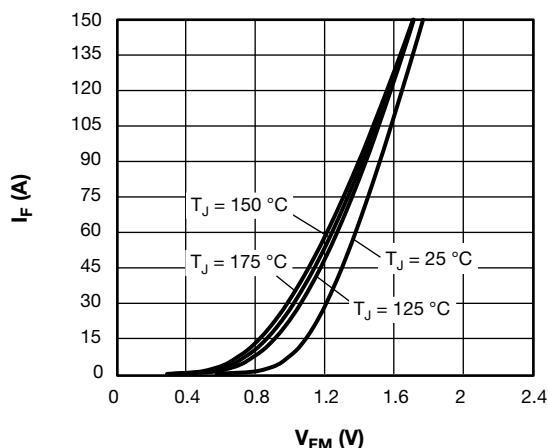


Fig. 29 - Typical D1 - D2 - D3 - D4 Antiparallel Diode Forward Characteristics

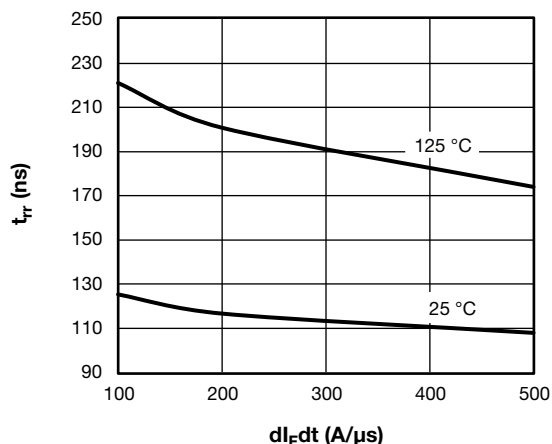


Fig. 31 - Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Time vs. dI_F/dt
 $V_{rr} = 200 \text{ V}$, $I_F = 50 \text{ A}$

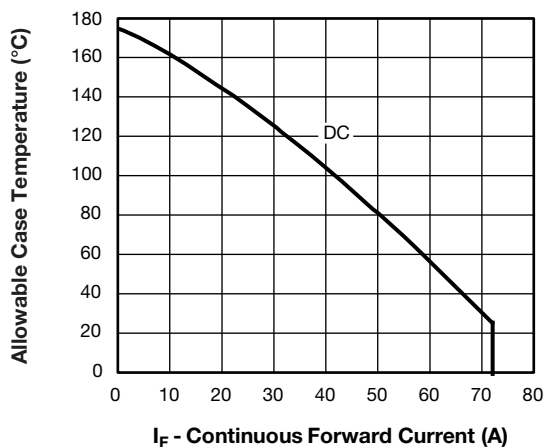


Fig. 30 - Maximum D1 - D2 - D3 - D4 Antiparallel Diode Forward Current vs. Case Temperature

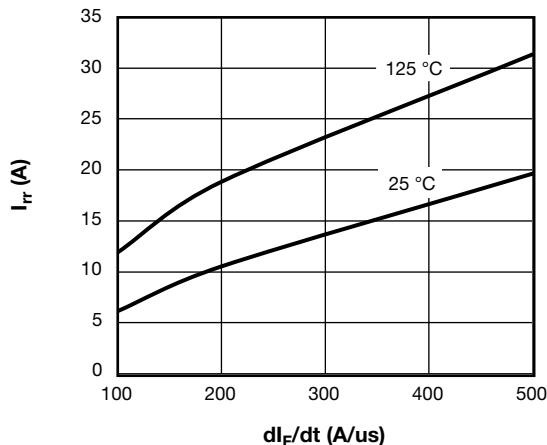


Fig. 32 - Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Current vs. dI_F/dt
 $V_{rr} = 200 \text{ V}$, $I_F = 50 \text{ A}$

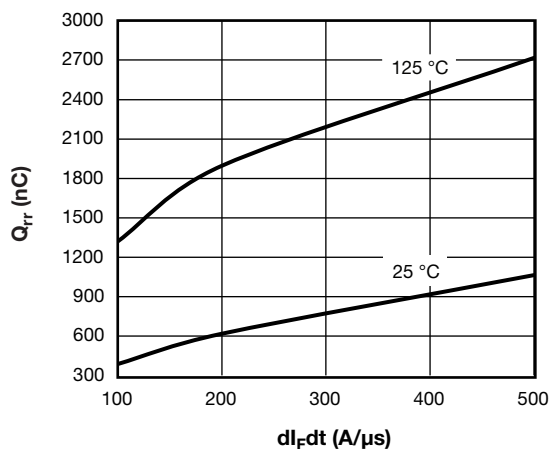


Fig. 33 - Typical D1 - D2 - D3 - D4 Antiparallel Diode Reverse Recovery Charge vs. dI_F/dt
 $V_{rr} = 200 \text{ V}$, $I_F = 50 \text{ A}$

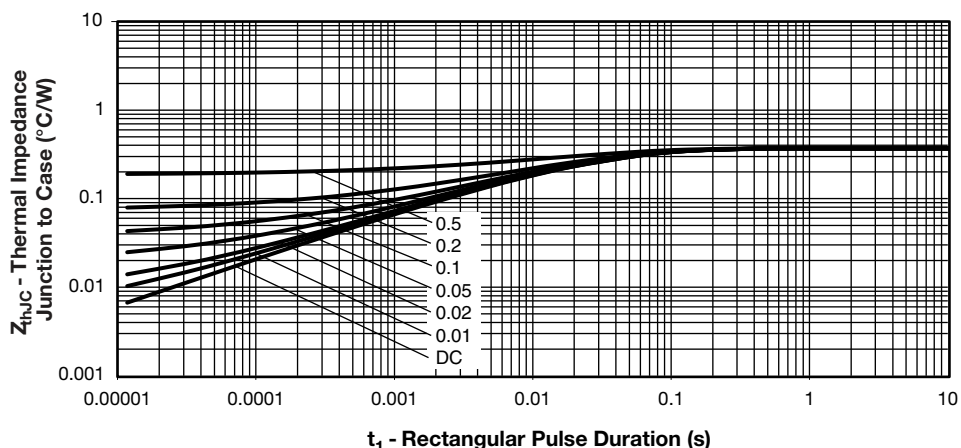


Fig. 34 - Maximum Thermal Impedance Z_{thJC} Characteristics
(Q2 - Q3 Trench IGBT)

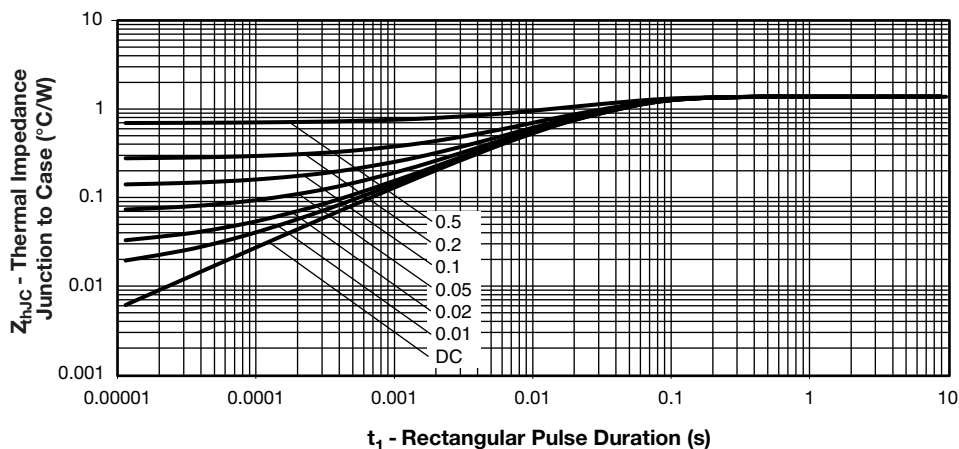


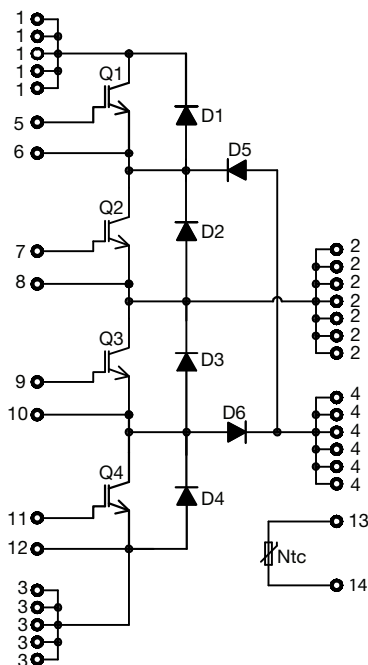
Fig. 35 - Maximum Thermal Impedance Z_{thJC} Characteristics
(D1 - D2 - D3 - D4 Antiparallel Diode)

ORDERING INFORMATION TABLE

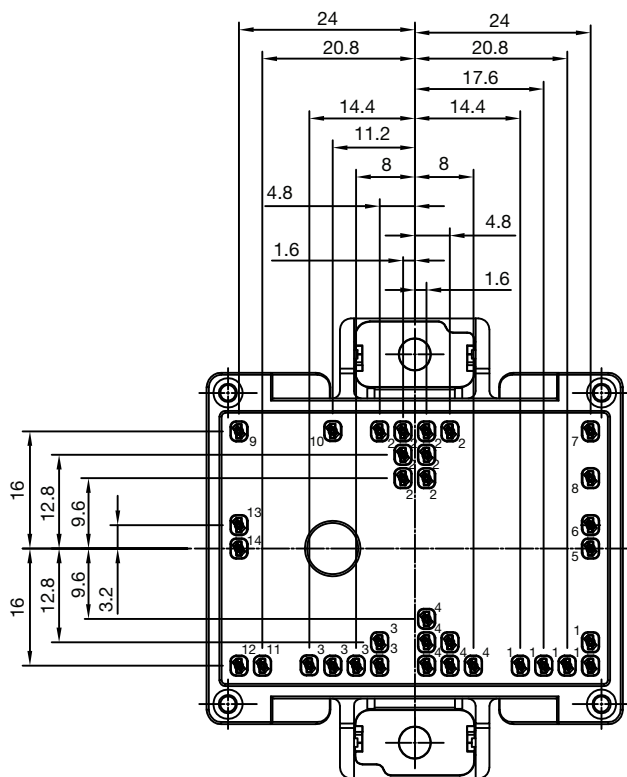
Device code	VS-	ET	F	075	Y	60	U
	①	②	③	④	⑤	⑥	⑦
1	-	Vishay Semiconductors product					
2	-	Package indicator (ET = EMIPAK-2B)					
3	-	Circuit configuration (F = 3-levels half-bridge inverter stage)					
4	-	Current rating (075 = 75 A)					
5	-	Switch die technology (Y = trench IGBT)					
6	-	Voltage rating (60 = 600 V)					
7	-	Diode die technology (U = ultrafast diode)					



CIRCUIT CONFIGURATION



PACKAGE



LINKS TO RELATED DOCUMENTS

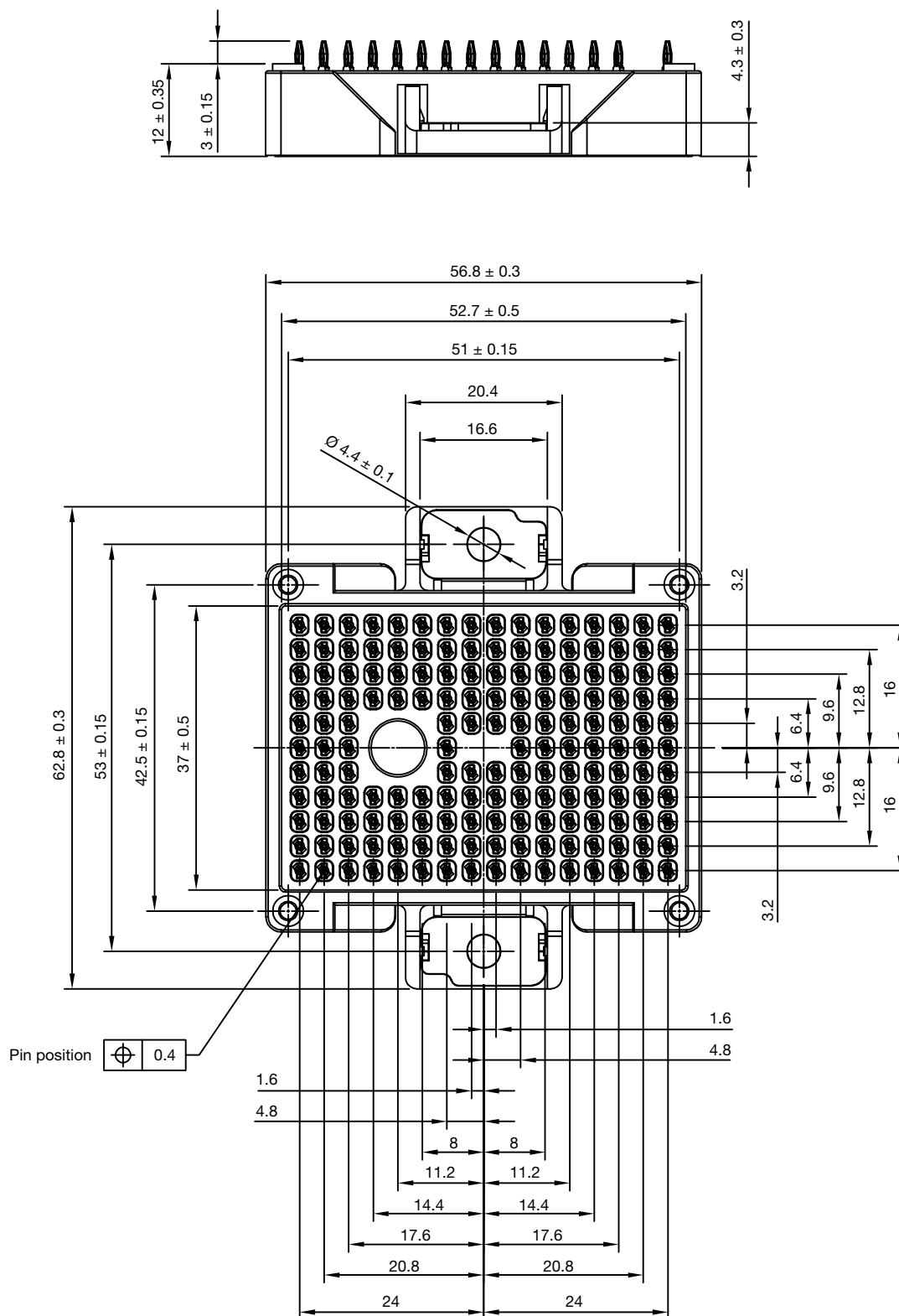
Dimensions

www.vishay.com/doc?95559



EMIPAK-2B PressFit

DIMENSIONS in millimeters





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